

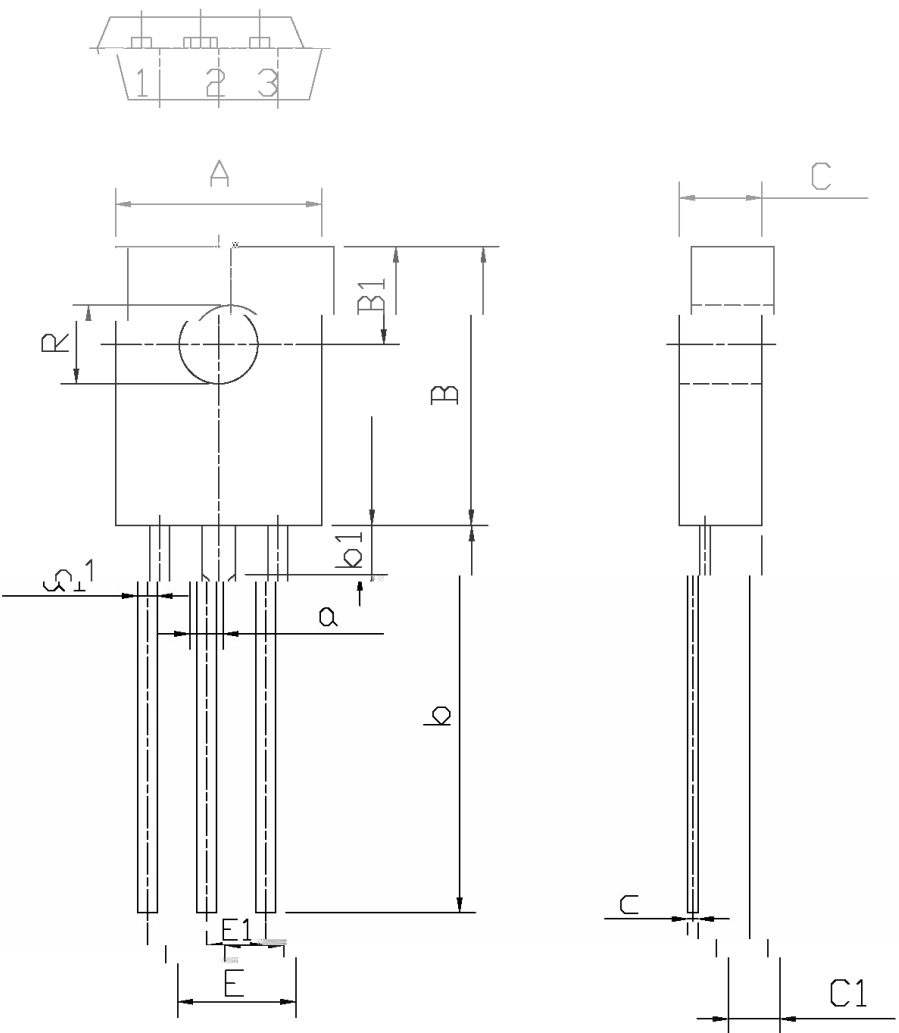
Silicon PNP transistor in a

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-110	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-2.5	A
Collector Power Dissipation	P_C	1.25	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

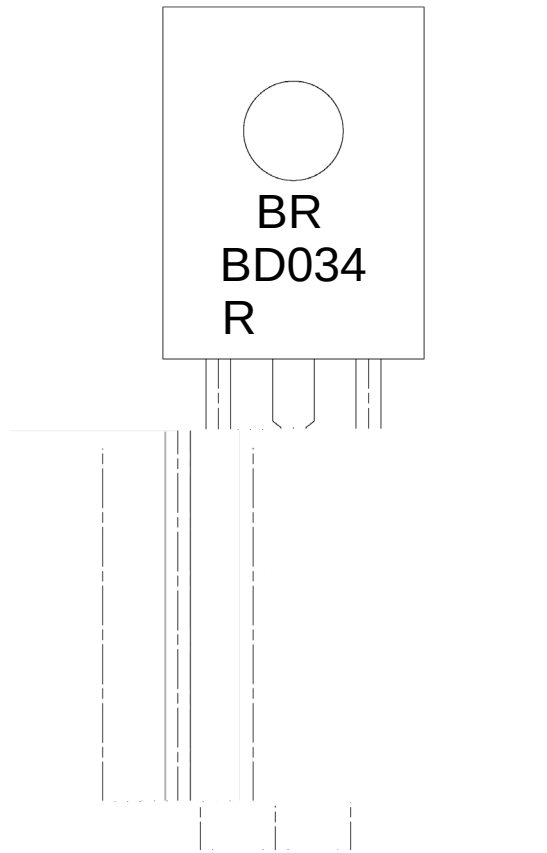
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A, I_B = 0$	-110			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10.5mA, I_B = 0$	-80			V

FW-126T

单位: mm



Symbol	Dimension in Millimeters		Symbol	Dimension in Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.65	0.85
B	10.8	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.95	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			



Note:

BR: Company Code

BD034: Product Type.

R h_{FE} Classifications Symbol

***: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255 5

5 0.5sec;

3

2 10

/sec.
- Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp.:270±5℃

Time:10±1 sec

/ BULK

Package Type	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
封装形式	只 套管	套管 盒	只 盒